

Radar Pulsed Power Transistor 55W, 1.2-1.4 GHz, 1ms Pulse, 10% Duty

M/A-COM Products Released, 30 May 07

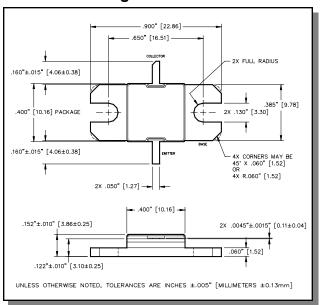
Features

- NPN silicon microwave power transistors
- · Common base configuration
- Broadband Class C operation
- High efficiency inter-digitized geometry
- · Diffused emitter ballasting resistors
- Gold metallization system
- · Internal input and output impedance matching
- Hermetic metal/ceramic package
- RoHS compliant

Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V_{CES}	58	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Collector Current (Peak)	I _C	7.0	Α
Power Dissipation @ +25°C	P _{TOT}	220	W
Storage Temperature	T _{STG}	-65 to +200	°C
Junction Temperature	T_J	200	°C

Outline Drawing



Electrical Specifications: T_C = 25 ± 5°C (Room Ambient)

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	I _C = 120mA		BV _{CES}	58	-	V
Collector-Emitter Leakage Current	V _{CE} = 28V		I _{CES}	-	6.0	mA
Thermal Resistance	Vcc = 28V, Pin = 12W	F = 1.2, 1.3, 1.4 GHz	R _{TH(JC)}	-	0.8	°C/W
Output Power	Vcc = 28V, Pin = 12W	F = 1.2, 1.3, 1.4 GHz	P _{OUT}	55	-	W
Power Gain	Vcc = 28V, Pin = 12W	F = 1.2, 1.3, 1.4 GHz	G _P	6.6	-	dB
Collector Efficiency	Vcc = 28V, Pin = 12W	F = 1.2, 1.3, 1.4 GHz	ης	50	-	%
Input Return Loss	Vcc = 28V, Pin = 12W	F = 1.2, 1.3, 1.4 GHz	RL	-	-10	dB
Load Mismatch Tolerance	Vcc = 28V, Pin = 12W	F = 1.2, 1.3, 1.4 GHz	VSWR-T	-	3:1	_
Load Mismatch Stability	Vcc = 28V, Pin = 12W	F = 1.2, 1.3, 1.4 GHz	VSWR-S	-	1.5:1	-

ADVANCED: Data Sheets contain information regarding a product M/A-COM Technology Solutions is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed.

PRELIMINARY: Data Sheets contain information regarding a product M/A-COM Technology Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available. Commitment to produce in volume is not guaranteed.

North America Tel: 800.366.2266 / Fax: 978.366.2266

[•] Europe Tel: 44.1908.574.200 / Fax: 44.1908.574.300

Asia/Pacific Tel: 81.44.844.8296 / Fax: 81.44.844.8298 Visit www.macomtech.com for additional data sheets and product information.

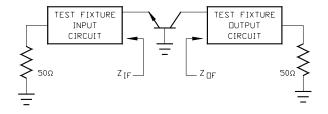


Radar Pulsed Power Transistor 55W, 1.2-1.4 GHz, 1ms Pulse, 10% Duty

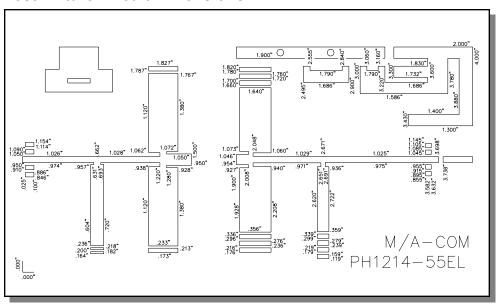
M/A-COM Products Released, 30 May 07

RF Test Fixture Impedance

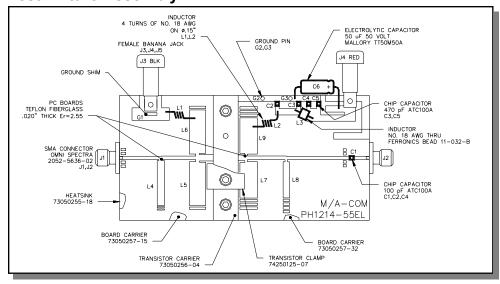
F (GHz)	Z _{IF} (Ω)	Z _{OF} (Ω)
1.2	5.8 + j1.8	5.5 - j3.4
1.3	2.4 + j1.3	3.3 - j2.3
1.4	2.4 + j0.6	2.0 - j2.3



Test Fixture Circuit Dimensions



Test Fixture Assembly



- ADVANCED: Data Sheets contain information regarding a product M/A-COM Technology Solutions is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed.

 PRELIMINARY: Data Sheets contain information regarding a product M/A-COM Technology
- PRELIMINARY: Data Sheets contain information regarding a product M/A-COM Technology Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available. Commitment to produce in volume is not guaranteed.
- North America Tel: 800.366.2266 / Fax: 978.366.2266
- Europe Tel: 44.1908.574.200 / Fax: 44.1908.574.300
- Asia/Pacific Tel: 81.44.844.8296 / Fax: 81.44.844.8298
 Visit www.macomtech.com for additional data sheets and product information.